

Interference Search History Print out M/T

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|--|---|------------------|---------|------------------|
| L1 | 3 | (non-volatile near memory and substrate and trench and gate and source/drain and dielectric and charge-trapping near layer).CLM. | US-PGPUB; USPAT; USOCR; EPO; JPO | OR | OFF | 2005/11/18 09:53 |